

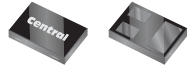
CEDM8004

**SURFACE MOUNT  
P-CHANNEL  
ENHANCEMENT-MODE  
SILICON MOSFET**



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**TLP**™  
Tiny  
Leadless  
Package



Top View Bottom View

**SOT-883L CASE**

• Devices are **Halogen Free** by design

**APPLICATIONS:**

- Load/Power switches
- Power supply converter circuits
- Battery powered portable devices

**MAXIMUM RATING:** (T<sub>A</sub>=25°C)

Drain-Source Voltage  
 Gate-Source Voltage  
 Continuous Drain Current  
 Power Dissipation  
 Operating and Storage Junction Temperature

**SYMBOL**

V<sub>DS</sub> 30  
 V<sub>GS</sub> 8.0  
 I<sub>D</sub> 450  
 P<sub>D</sub> 100  
 T<sub>J</sub>, T<sub>stg</sub> -65 to +150

**UNITS**

V  
 V  
 mA  
 mW  
 °C

**ELECTRICAL CHARACTERISTICS:** (T<sub>A</sub>=25°C unless otherwise noted)

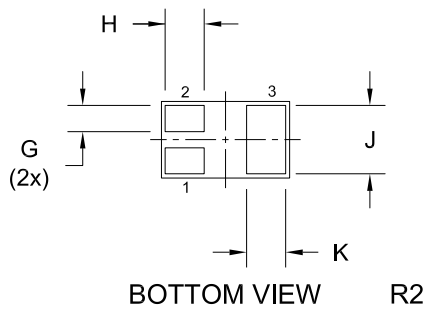
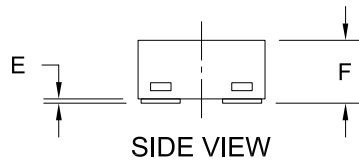
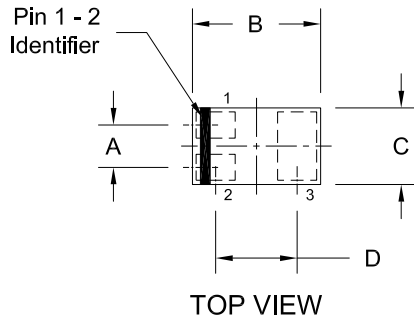
SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>GSSF</sub> , I <sub>GSSR</sub>	V <sub>GS</sub> =8.0V, V <sub>DS</sub> =0			3.0	μA
I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0			1.0	μA
BV <sub>DSS</sub>	V <sub>GS</sub> =0, I <sub>D</sub> =100μA	30			V
V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5		1.0	V
V <sub>SD</sub>	V <sub>GS</sub> =0, I <sub>S</sub> =100mA			1.1	V
r <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =430mA		1.0	1.1	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =200mA		1.6	2.0	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =1.8V, I <sub>D</sub> =100mA		2.6	3.3	Ω
g <sub>FS</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =100mA	200			mS
C <sub>rss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0, f=1.0MHz		8.9	10	pF
C <sub>iSS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0, f=1.0MHz		45	55	pF
C <sub>oss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0, f=1.0MHz		8.5	15	pF
Q <sub>g(tot)</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.0A		0.88		nC
Q <sub>gs</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.0A		0.35		nC
Q <sub>gd</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.0A		0.128		nC

R4 (1-November 2012)

**CEDM8004**  
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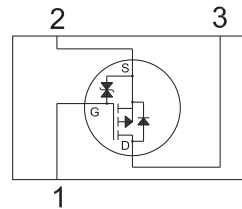
**SOT-883L CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.014		0.35	
B	0.037	0.041	0.95	1.05
C	0.022	0.026	0.55	0.65
D	0.026		0.65	
E	0.000	0.002	0.00	0.05
F	0.012	0.016	0.30	0.40
G	0.005	0.007	0.13	0.18
H	0.008	0.012	0.20	0.30
J	0.018	0.022	0.45	0.55
K	0.008	0.012	0.20	0.30

SOT-883L (REV:R2)

**PIN CONFIGURATION**  
**(Bottom View)**



**LEAD CODE:**

- 1) Gate
- 2) Source
- 3) Drain

**MARKING CODE: V**

R4 (1-November 2012)